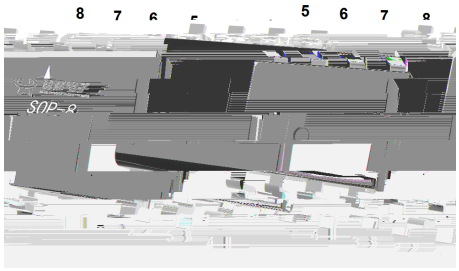
9 5 6 .> / / x 6 ?ú 3 3 5 9 « | • ’ož
P-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

V_{DS} (V) = -30V I_D = -16A (V_{GS} = ± 20V)
$R_{DS(ON)}$@-10V ”8.0m (Typ.7.0m)
$R_{DS(ON)}$@-4.5V ”15m (Typ.10.3m)
—)í D }ož HF Product.

9 › ’ ò k Ž ` ” — Õ y P ^ © Ïož
Power Management in Notebook computer, Portable Equipment and Battery powered systems.



PIN1 y S PIN 2 y S PIN 3 y S PIN 4 y G
PIN 5 y

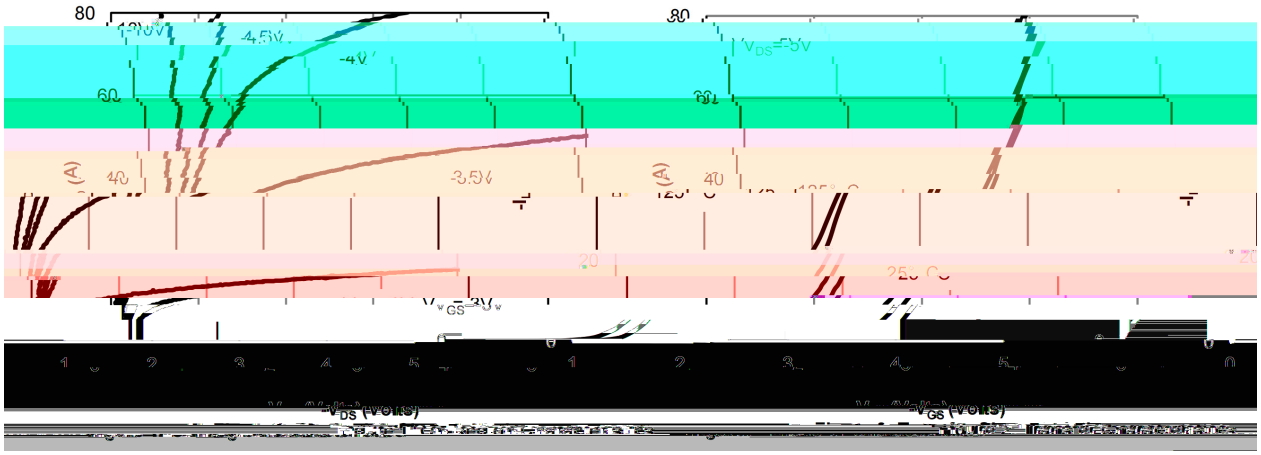
@ ƒ Parameter		… Z Symbol	ƒ › Rating	% y Unit
Drain-Source Voltage		V_{DS}	-30	V
Drain Current - Continuous		I_D	-16	A
Drain Current – Pulsed		I_{DM}	-65	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D	3	W
Single Pulse Avalanche Energy(L=0.5mH)		E_{AS}	360	mJ
Avalanche Current(L=0.5mH)		I_{AS}	-30	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	-
Thermal resistance, junction - ambient	t 0 10s	R JA	41.7	- / W
	Steady-State		75	

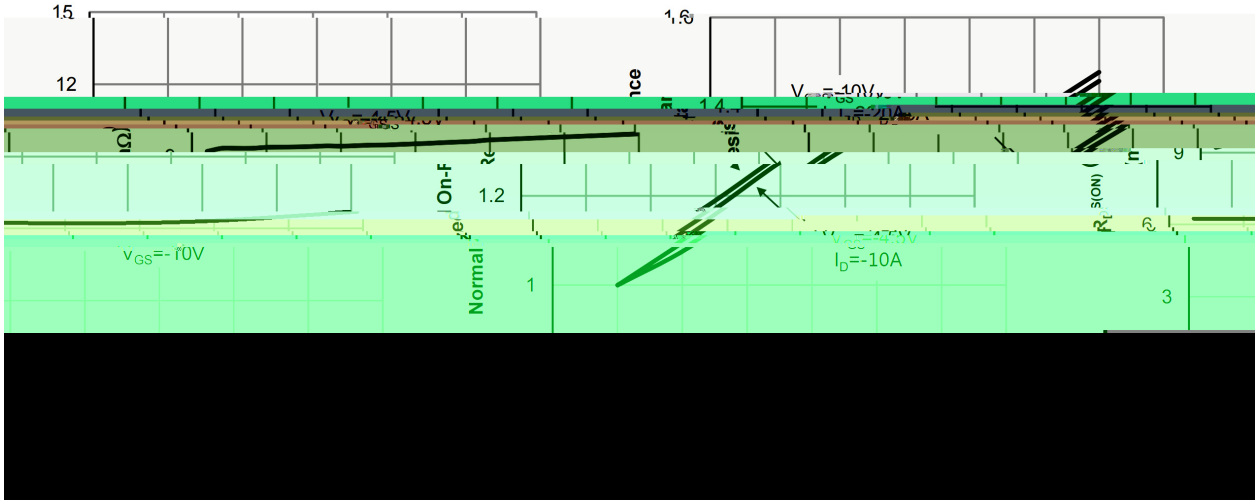
@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=-250 A V_{GS}=0V	-30	-35		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V V_{GS}=0V			-1	uA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}= ±20V			f 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=VGS I_D=-250 A	-1	-1.5	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-10A		7.0	8	m S
		V_{GS}=-4.5V, I_D=-8A		10.3	15	
Diode Forward Voltage	V_{SD}	I_S=-1A, V_{GS}=0V			-1.2	V
Input Capacitance	C_{iss}	V_{DS}=-25V V_{GS}=0V f=1.0MHz		3260		pF
Output Capacitance	C_{oss}			335		

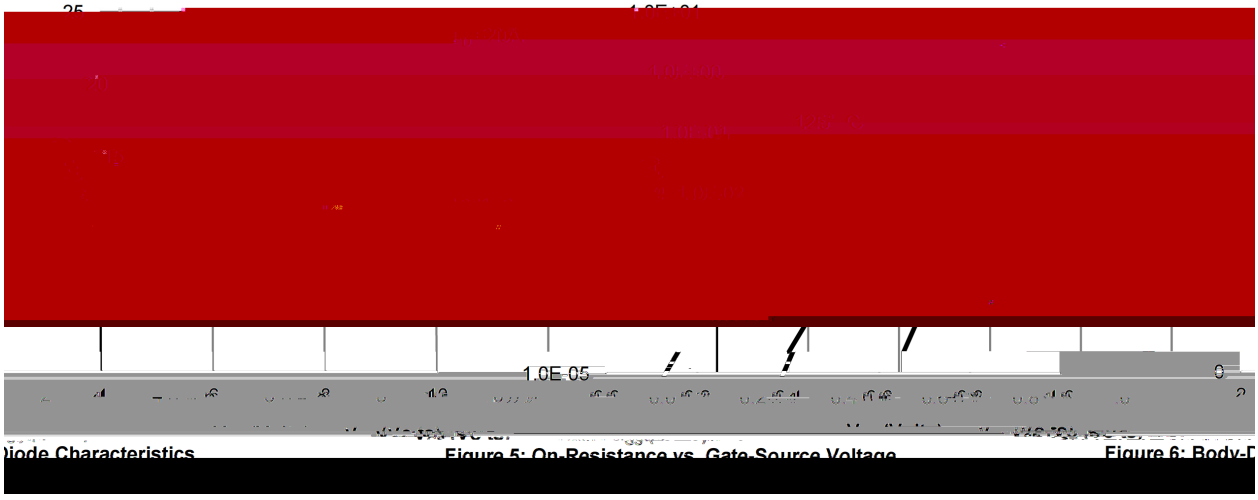
Ô4ì × ? d / Electcal Chaacteiscs(Ta=25 ;)

@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=-10V V_{DS}=-15V R_L=0.75 ¡ R_{GEN}=3 ¡		12.5		ns
Turn-On Rise Time	t_r			19		
Turn-Off Delay Time	$t_{d(off)}$			125		
Turn-Off Fall Time	t_f			67		

Ô ? d • Ž ¢ / Electcal Chaaceitic Cu

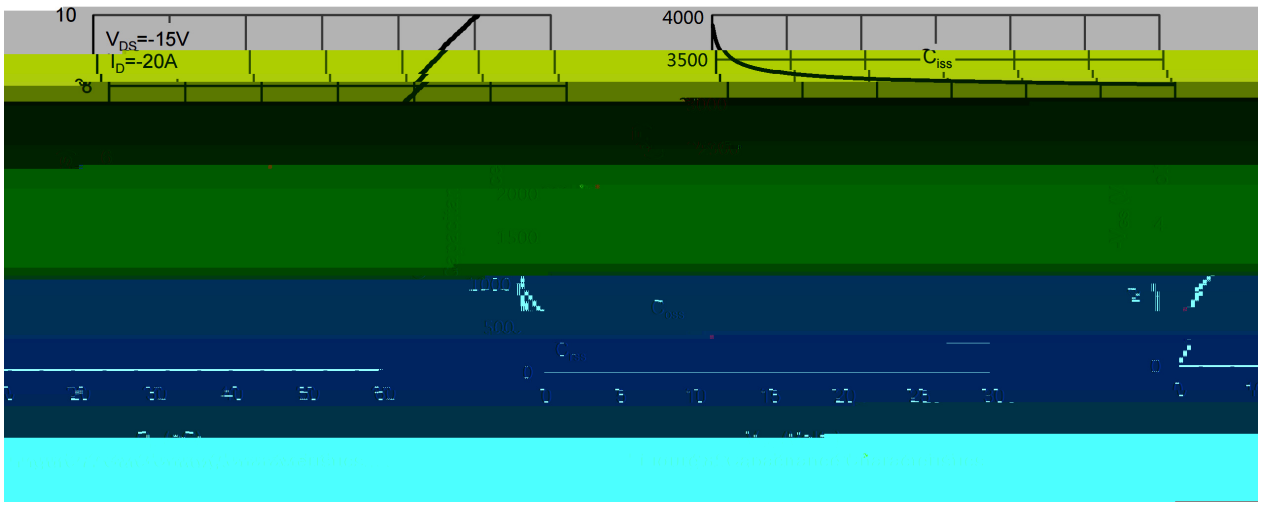


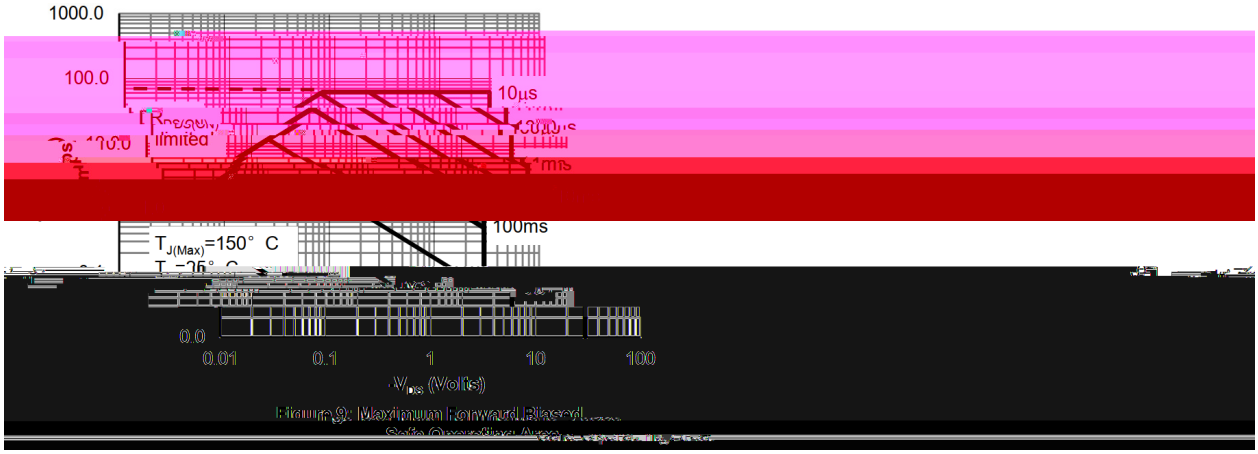


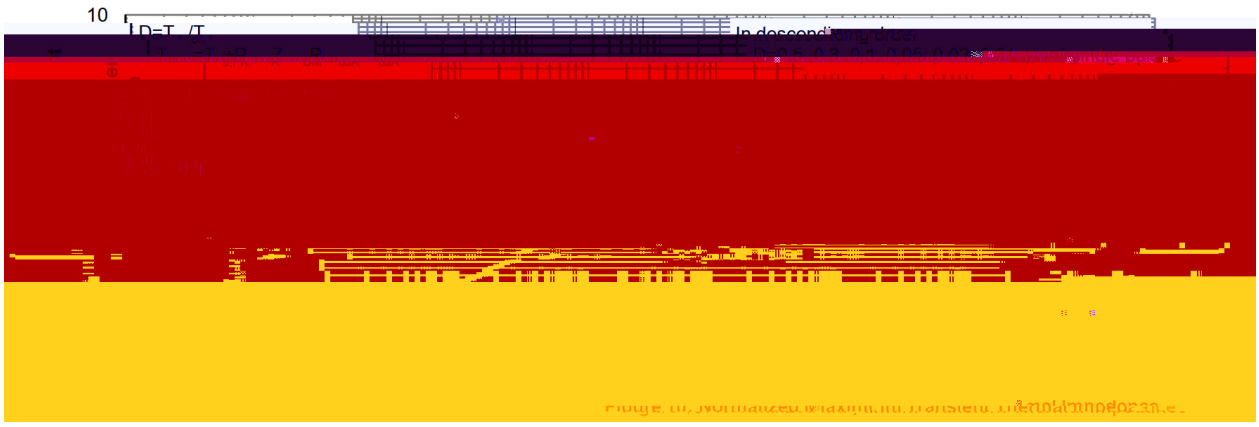


iode Characteristics Figure 5: On-Resistance vs. Gate-Source Voltage Figure 6: Body-D

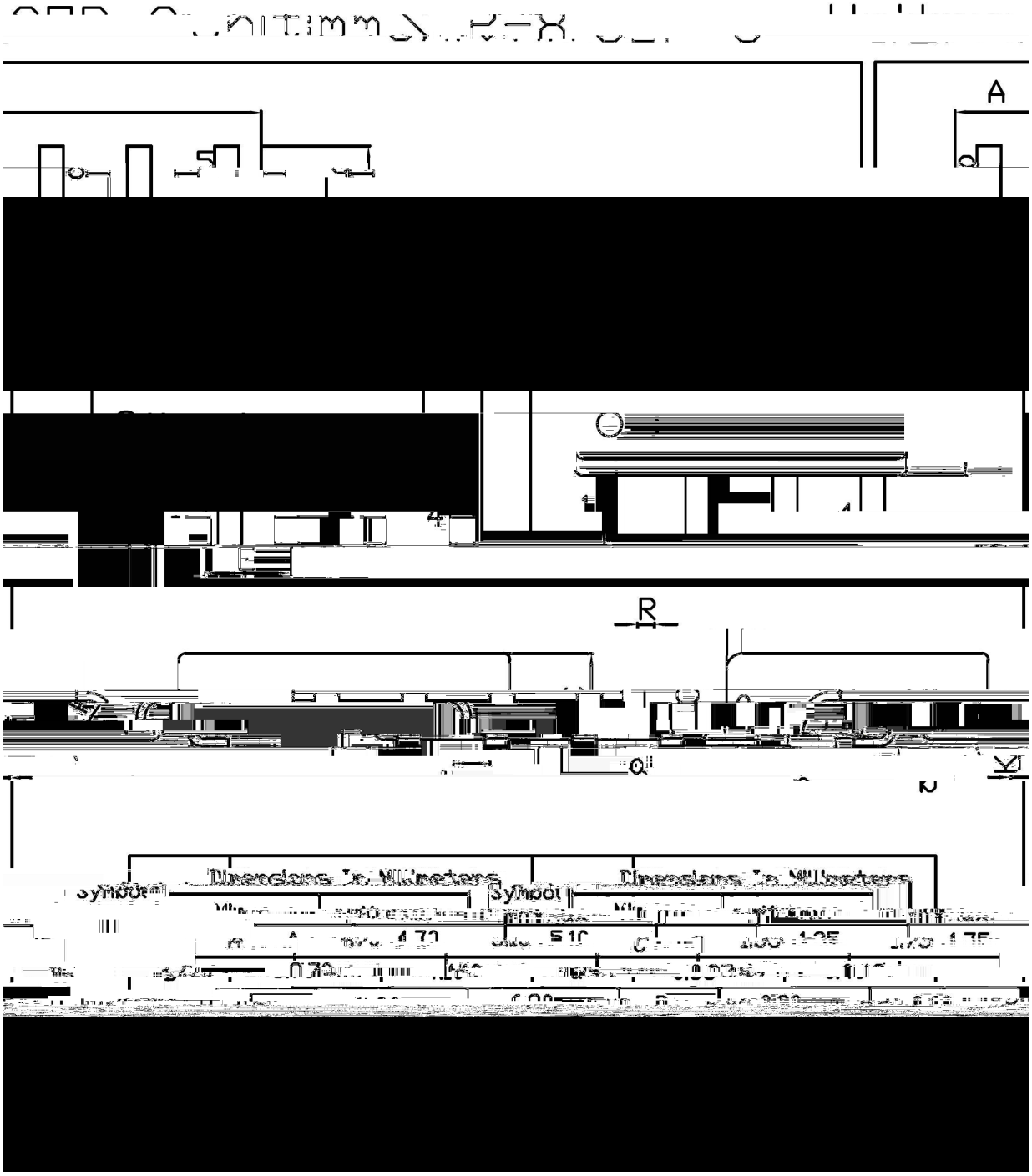
Ô ? d • Ž ¢ Electical Chaacteis Cu



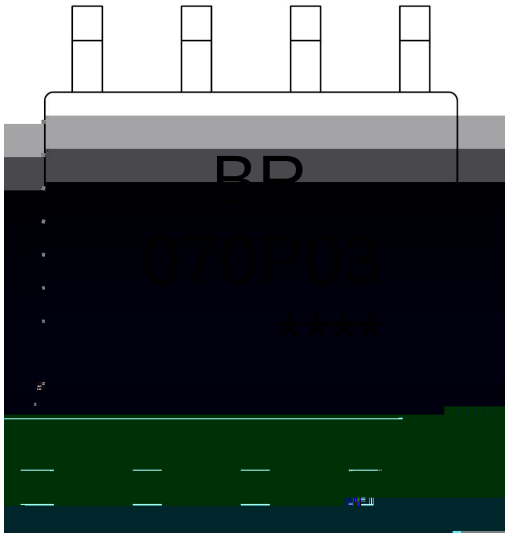




Ø ¤ =) ¢ / Package Dimensions



, M y ƒ / Making Intons



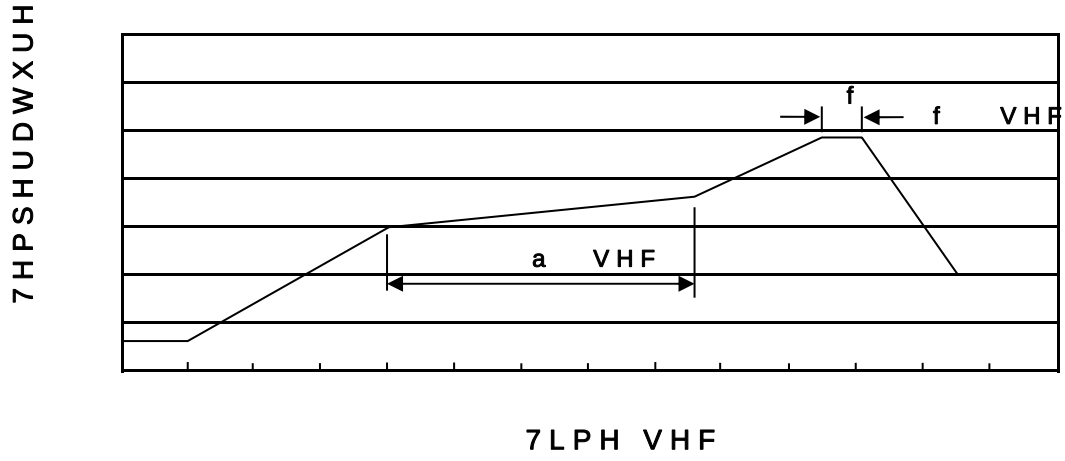
ª ¢ y

BR y	¸ [W A
070P03 y	º Z W A
**** y	ÿ D Z W A k š ÿ D Z J

Note:

BR:	Company Code
070P03:	Product Type Code
****:	Lot No. Code, code change with Lot No

š WD t … • Ž ¢ (x /) / : K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6



ª ¢ y

1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

2o• Q › “ † 245 r5 - k ž • 4 Ò 5 r0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »] / Reistance to Soldeing HeatTest Conditons

“ † y 260 r5 - ž • y 10 r1 sec. Temp.:260±5 Time:10±1 sec

G P á / Packaging SPEC.

2 & x / REEL

Package Type 7>û ˜ E	Units ;>û ¦H					Dimension ;>û p . (unit Æmm³)		
	Units/Reel / --	Reels/Inner Box -- /-	Units/Inner Box /-	Inner Boxes/Outer Box - /1ç	Units/Outer Box /1ç	Reel	Inner Box×	Outer Box1ç
SOP/ESOP-8	4,000	2	8,000	6	48,000	13 s ×12	360×360×50	380×335×366

„ Ð y ƒ / Notices